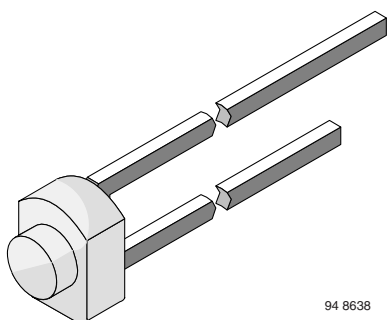


## Infrared Emitting Diode, RoHS Compliant, 950 nm, GaAs



### FEATURES

- Package type: leaded
- Package form: T-¾
- Dimensions (in mm):  $\varnothing$  1.8
- Peak wavelength:  $\lambda_p = 950$  nm
- High reliability
- Angle of half intensity:  $\varphi = \pm 55^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Package matches with detector BPW16N
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### DESCRIPTION

CQY36N is an infrared, 950 nm emitting diode in GaAs technology molded in a miniature, clear plastic package without lens.

### APPLICATIONS

- Radiation source in near infrared range

### PRODUCT SUMMARY

| COMPONENT | $I_e$ (mW/sr) | $\varphi$ (deg) | $\lambda_p$ (nm) | $t_r$ (ns) |
|-----------|---------------|-----------------|------------------|------------|
| CQY36N    | 1.5           | $\pm 55$        | 950              | 800        |

#### Note

Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS                      | PACKAGE FORM |
|---------------|-----------|------------------------------|--------------|
| CQY36N        | Bulk      | MOQ: 5000 pcs, 5000 pcs/bulk | T-¾          |

#### Note

MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS

| PARAMETER                           | TEST CONDITION       | SYMBOL     | VALUE         | UNIT       |
|-------------------------------------|----------------------|------------|---------------|------------|
| Reverse voltage                     |                      | $V_R$      | 5             | V          |
| Forward current                     |                      | $I_F$      | 100           | mA         |
| Surge forward current               | $t_p \leq 100 \mu s$ | $I_{FSM}$  | 2             | A          |
| Power dissipation                   |                      | $P_V$      | 160           | mW         |
| Junction temperature                |                      | $T_j$      | 100           | $^\circ C$ |
| Operating temperature range         |                      | $T_{amb}$  | - 25 to + 85  | $^\circ C$ |
| Storage temperature range           |                      | $T_{stg}$  | - 25 to + 100 | $^\circ C$ |
| Soldering temperature               | $t \leq 3 s$         | $T_{sd}$   | 245           | $^\circ C$ |
| Thermal resistance junction/ambient | leads not soldered   | $R_{thJA}$ | 450           | K/W        |

#### Note

$T_{amb} = 25^\circ C$ , unless otherwise specified

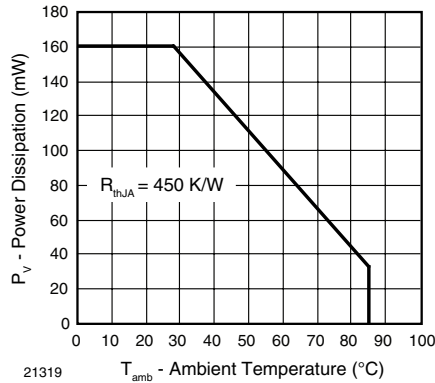


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

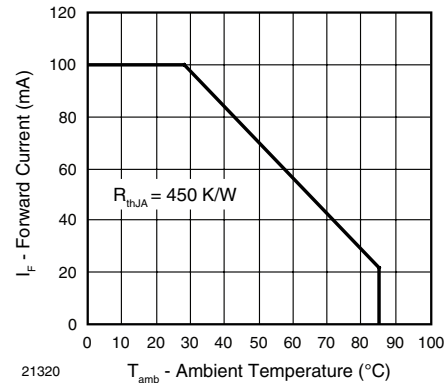


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS               |                                                                             |                 |      |          |      |               |
|-------------------------------------|-----------------------------------------------------------------------------|-----------------|------|----------|------|---------------|
| PARAMETER                           | TEST CONDITION                                                              | SYMBOL          | MIN. | TYP.     | MAX. | UNIT          |
| Forward voltage                     | $I_F = 50 \text{ mA}$ , $t_p \leq 20 \text{ ms}$                            | $V_F$           |      | 1.3      | 1.6  | V             |
| Temperature coefficient of $V_F$    | $I_F = 100 \text{ mA}$                                                      | $TK_{V_F}$      |      | - 1.3    |      | mV/K          |
| Breakdown voltage                   | $I_R = 100 \text{ } \mu\text{A}$                                            | $V_{(BR)}$      | 5    |          |      | $\mu\text{A}$ |
| Junction capacitance                | $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$ , $E = 0$                         | $C_j$           |      | 50       |      | pF            |
| Radiant intensity                   | $I_F = 50 \text{ mA}$ , $t_p \leq 20 \text{ ms}$                            | $I_e$           | 0.7  | 1.5      | 7.5  | mW/sr         |
| Radiant power                       | $I_F = 50 \text{ mA}$ , $t_p \leq 20 \text{ ms}$                            | $\phi_e$        |      | 10       |      | mW            |
| Temperature coefficient of $\phi_e$ | $I_F = 50 \text{ mA}$                                                       | $TK_{\phi_e}$   |      | - 0.8    |      | %/K           |
| Angle of half intensity             |                                                                             | $\varphi$       |      | $\pm 55$ |      | deg           |
| Peak wavelength                     | $I_F = 50 \text{ mA}$                                                       | $\lambda_p$     |      | 950      |      | nm            |
| Spectral bandwidth                  | $I_F = 50 \text{ mA}$                                                       | $\Delta\lambda$ |      | 50       |      | nm            |
| Rise time                           | $I_F = 100 \text{ mA}$                                                      | $t_r$           |      | 800      |      | ns            |
|                                     | $I_F = 1.5 \text{ A}$ , $t_p/T = 0.01$ , $t_p \leq 10 \text{ } \mu\text{s}$ | $t_r$           |      | 400      |      | ns            |
| Virtual source diameter             |                                                                             | $d$             |      | 1.2      |      | mm            |

#### Note

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

#### BASIC CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

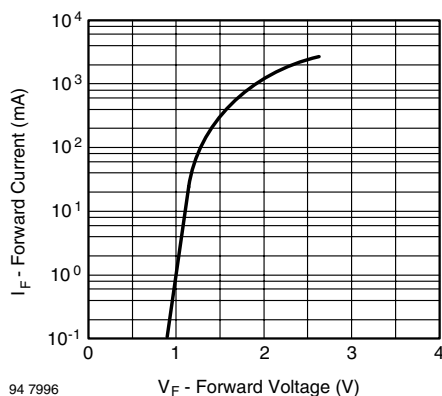


Fig. 3 - Forward Current vs. Forward Voltage

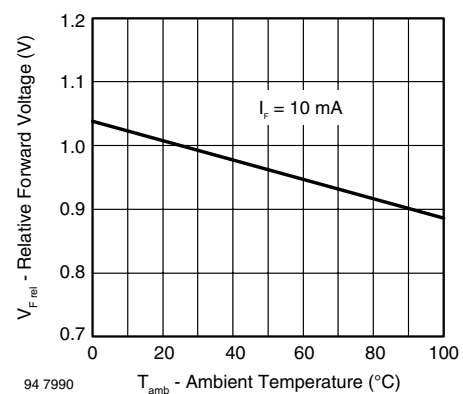


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

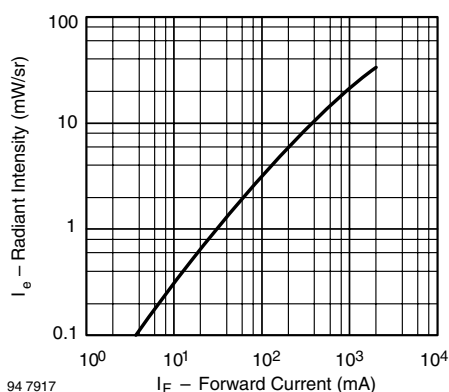


Fig. 5 - Radiant Intensity vs. Forward Current

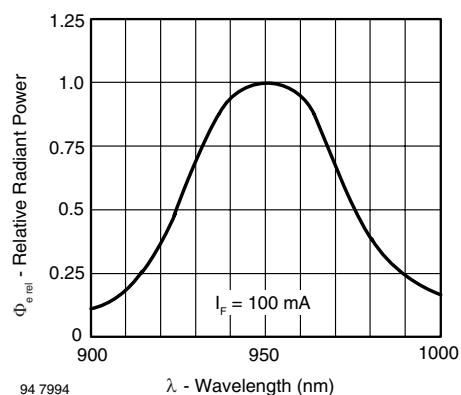


Fig. 8 - Relative Radiant Power vs. Wavelength

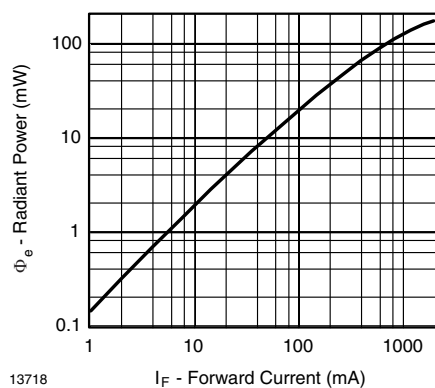


Fig. 6 - Radiant Power vs. Forward Current

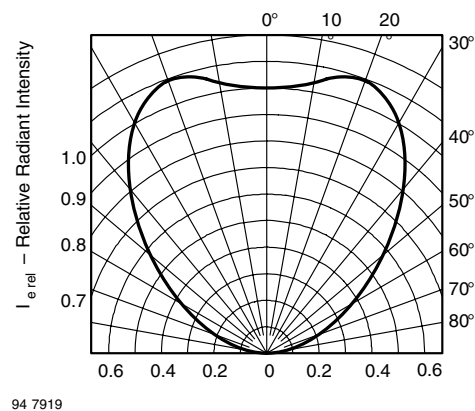


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

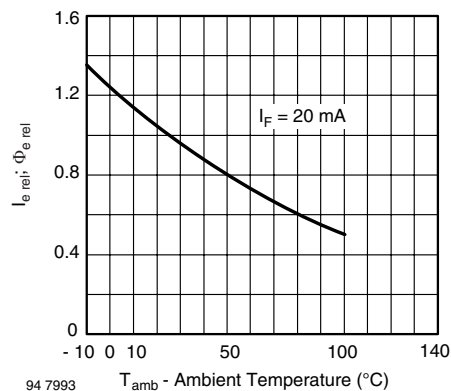
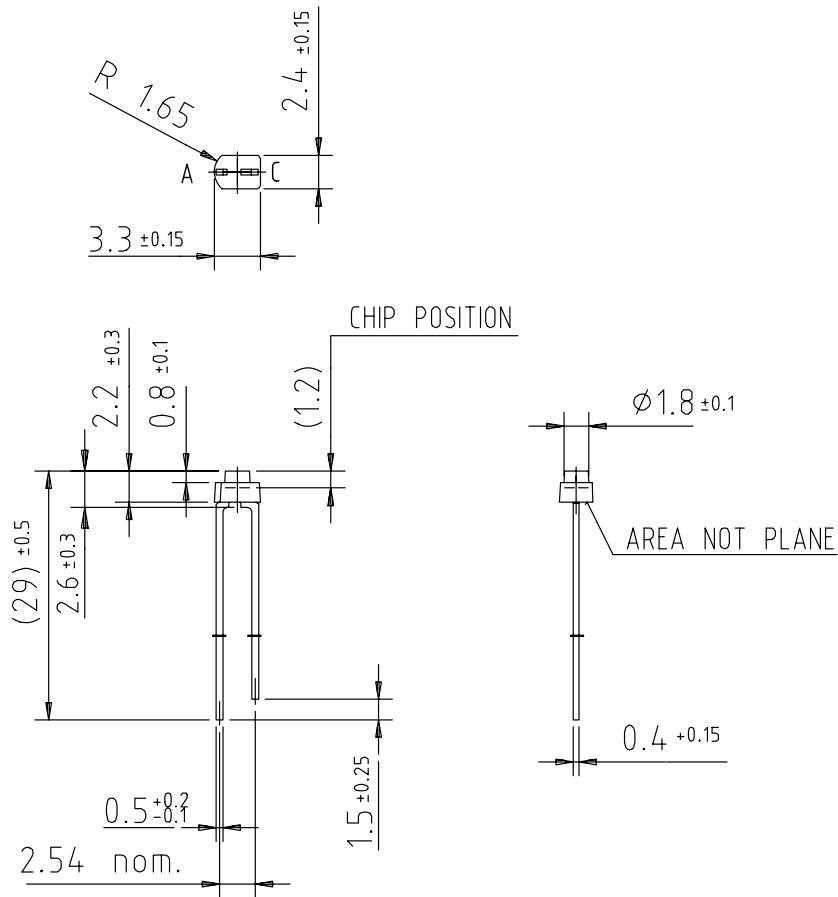


Fig. 7 - Relative Radiant Intensity/Power vs. Ambient Temperature

**PACKAGE DIMENSIONS** in millimeters

96 12189

technical drawings  
according to DIN  
specifications



### Disclaimer

All product specifications and data are subject to change without notice.

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